



SSC8415GS6B

P-Channel Enhancement Mode MOSFET

➤ Features

V _{DS}	V _{GS}	R _{DS(ON)} Typ.	I _D
-20V	±12V	41mΩ @-4V5	-3.7A
		54mΩ @-2V5	

➤ Description

This device is produced with high cell density DMOS trench technology, which is especially used to minimize on-state resistance. This device particularly suits low voltage applications such as portable equipment, power management and other battery powered circuits, and low in-line power dissipation are needed in a very small outline surface mount package.

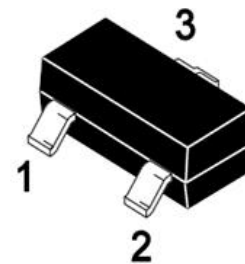
➤ Applications

- Load Switch
- Portable Devices
- DCDC Conversion

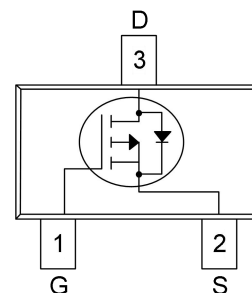
➤ Ordering Information

Device	Package	Shipping
SSC8415GS6B	SOT-23	3000/Reel

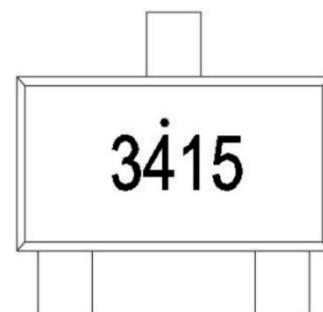
➤ Pin configuration



SOT-23



Pin Configuration (Top View)



Marking



➤ **Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)**

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain-to-Source Voltage	-20	V
V_{GSS}	Gate-to-Source Voltage	± 12	V
I_D	Continuous Drain Current ^a	-3.7	A
I_{DM}	Pulsed Drain Current ^b	-15	A
P_D	Power Dissipation ^c	0.9	W
T_J	Operation junction temperature	-55 to 150	$^\circ\text{C}$
T_{STG}	Storage temperature range	-55 to 150	$^\circ\text{C}$

➤ **Thermal Resistance Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)**

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance ^a	140	$^\circ\text{C/W}$

Note:

- The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz.copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user is specific board design. The power dissipation is based on the $t \leq 10\text{s}$ thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation P_D is based on $T_{J(MAX)}=150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

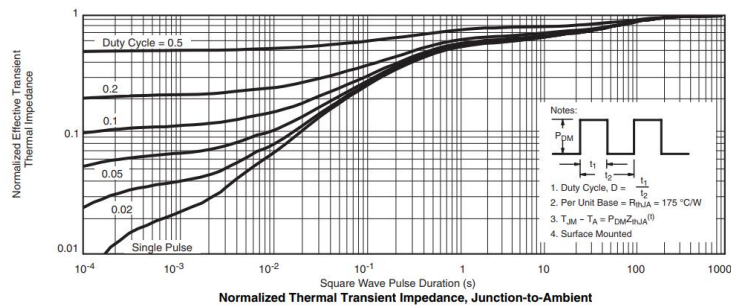
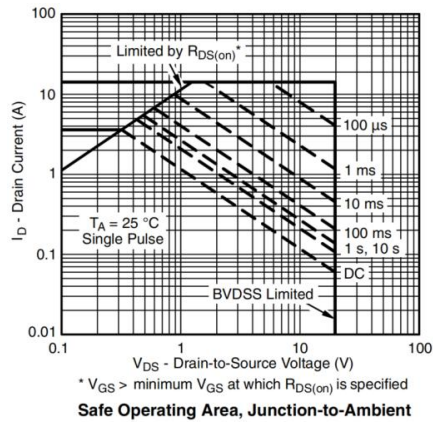
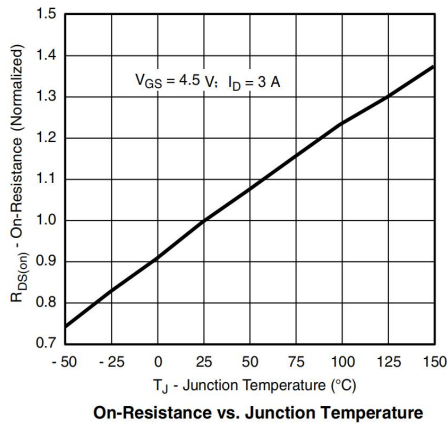
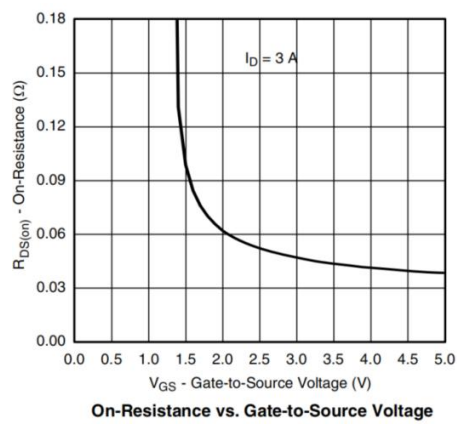
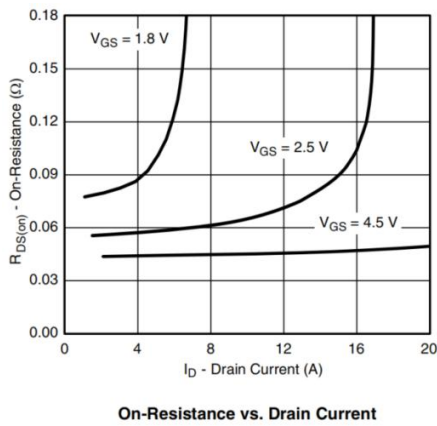
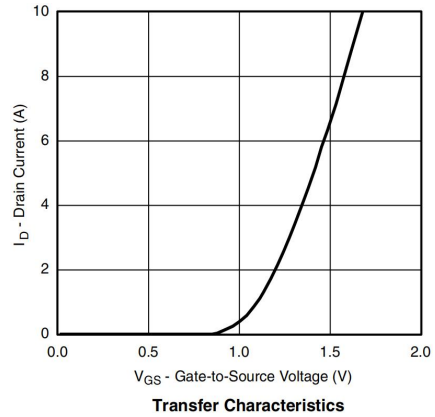
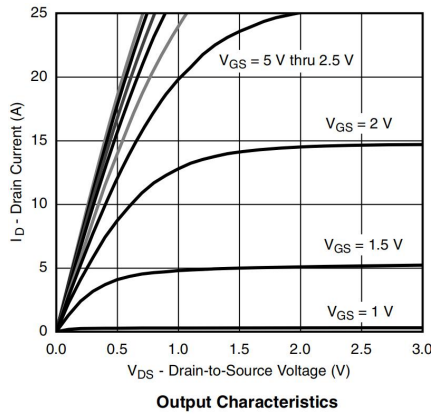


➤ **Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)**

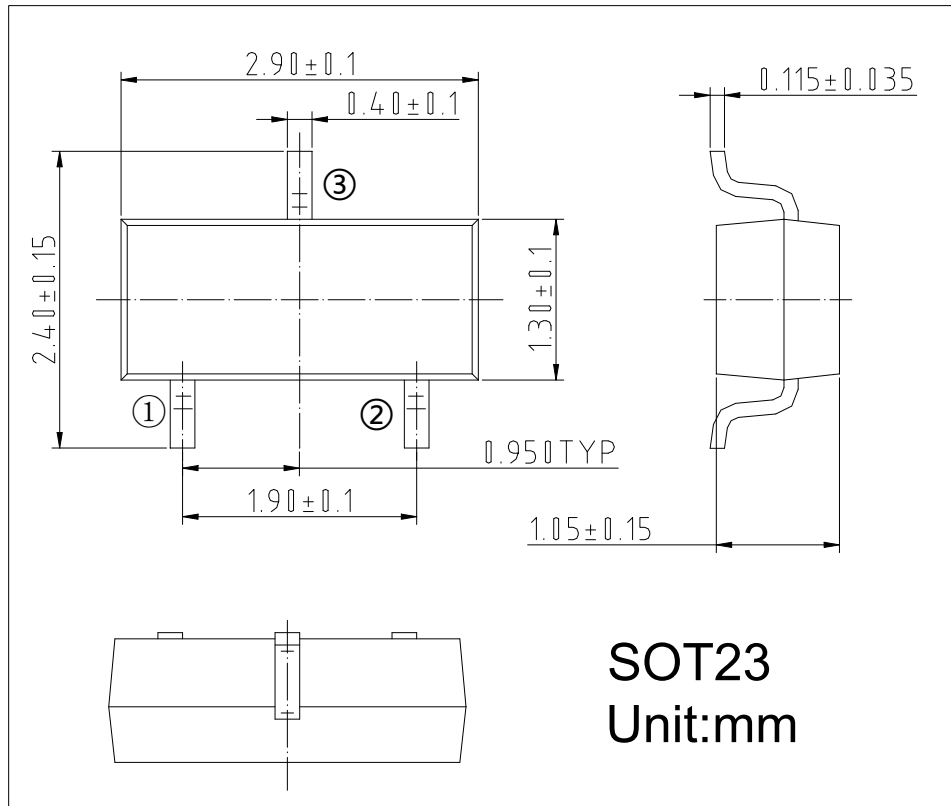
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-10\mu A$	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.6	-1	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-3.5A$		41	53	m Ω
		$V_{GS}=-2.5V, I_D=-3A$		54	70	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$			-1	μA
Gate-Source Leak Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$			± 100	nA
Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=-1.6A$	-0.5	-0.75	-1.2	V
Input Capacitance	C_{ISS}	$V_{DS} = -10V, V_{GS} = 0V,$ $f = 1MHz$		869		pF
Output Capacitance	C_{OSS}			265		
Reverse Transfer Capacitance	C_{RSS}			258		
Turn-on Delay Time	$T_{D(ON)}$	$V_{DS}=-10V,$ $I_D=-1.0A, R_L=6\Omega,$ $V_{GS}=-4.5V, R_G=6\Omega,$		12		ns
Rise Time	T_r			8.9		
Turn-off Delay Time	$T_{D(OFF)}$			45		
Fall Time	T_f			15		
Total Gate Charge	Q_G	$V_{DS}=-10V, V_{GS}=-4.5V,$ $I_D=-5A$		12		nC
Gate to Source Charge	Q_{GS}			2.1		
Gate to Drain Charge	Q_{GD}			2.4		



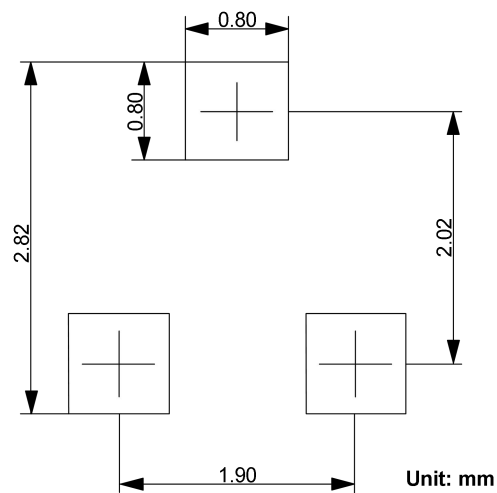
➤ Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)



➤ Package Information



➤ Recommended Pad outline





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